

RoHS

COMPLIANT

4 $\Omega,$ 360 MHz, Dual SPST Analog Switches

DESCRIPTION

The DG3537, DG3538, DG3539, DG3540 are dual SPST analog switches which operate from 1.8 V to 5.5 V single rail power supply. They are design for audio, video, and USB switching applications.

The devices have 4 Ω on-resistance and 360 MHz 3 dB bandwidth. 0.2 Ω on-resistance matching and 1 Ω flatness make the device high linearity. The devices are 1.6 V logic compatible within the full operation voltage range.

These switches are built on a sub-micron high density process that brings low power consumption and low voltage performance.

The switches are packaged in MICRO FOOT chip scale package of 3×3 bump array.

As a committed partner to the community and environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switch products manufactured with tin/silver/copper (SnAgCu) device termination, the lead (Pb)-free "-E1" suffix is being used as a designator.

FEATURES

- 1.8 V to 5.5 V operation
- 3 Ω at 2.7 V R_{ON}
- 360 MHz 3 dB bandwidth

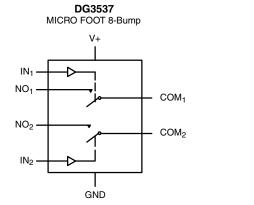
• 1.6 V logic compatible

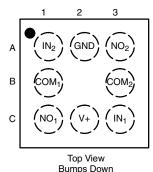
- ESD method 3015.7 > 2 kV
- Latch-up current 0.300 mA (JESD 78)
- BENEFITS
- Space saving MICRO FOOT[®] package
- High linearity
- Low power consumption
- High bandwidth
- Full rail Signal swing range

APPLICATIONS

- · Cellular phones
- MP3
 - Media players
 - Modems
 - Hard drives
 - PCMCIA

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





Device Marking

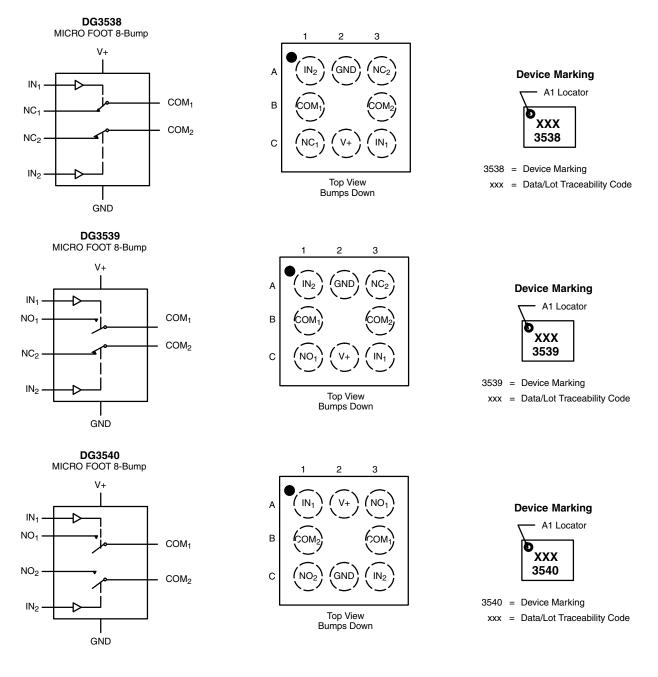




3537 = Device Marking xxx = Data/Lot Traceability Code



FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE						
Logic	NC1 and NC2	NO1 and NO2				
0	ON	OFF				
1	OFF	ON				

ORDERING INFORMATION							
Temp. Range	Package	Part Number					
- 40 °C to 85 °C	MICRO FOOT: 8 Bump (3 x 3, 0.5 mm Pitch, 238 µm Bump Height)	DG35337DB-T5-E1 DG3538DB-T5-E1 DG3539DB-T5-E1 DG3540DB-T1-E1					



ABSOLUTE MAXIMUM RATINGS						
Parameter		Limit	Unit			
Reference V+ to GND	- 0.3 to + 6	N/				
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3 V)	V			
Continuous Current (NO, NC, COM)	± 100	mA				
Peak Current (Pulsed at 1 ms, 10 % duty	/ cycle)	± 200	IIIA			
Storage Temperature	(D Suffix)	- 65 to 150	**			
Package Solder Reflow Conditions ^b	IR/Convection	250	°C			
ESD per Method 3015.7	·	> 2	kV			
Power Dissipation (Packages) ^c	MICRO FOOT: 8 Bump (3 x 3 mm) ^d	400	mW			

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. Refer to IPC/JEDEC (J-STD-020B)

c. All bumps welded or soldered to PC Board.

d. Derate 5.0 mW/°C above 70 °C.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+ :	= 3 V)						
		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °C		5°C	
Parameter	Symbol	V+ = 2.7 to 3.6 V, V_{IN} = 0.5 V or 1.4 V ^e	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Analog Switch			-				
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	v
On-Resistance ^d	R _{ON}		Room Full		3	4 4.3	
R _{ON} Flatness ^d	R _{ON} Flatness	V + = 2.7 V, V_{COM} = 0.2/1.5 V I_{NO} , I_{NC} = 10 mA	Room		0.75	1.2	Ω
On-Resistance Match Between Channels ^d	$\Delta R_{DS(on)}$		Room			0.25	
Switch Off Lookage Current	I _{NO(off)} I _{NC(off)}	V+ = 3.6 V,	Room Full	- 2 - 20		2 20	nA
Switch Off Leakage Current ^r	I _{COM(off)}	V_{NO} , V_{NC} = 0.3 V/3.3 V, V_{COM} = 3.3 V/0.3 V	Room Full	- 2 - 20		2 20	
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 3.6 V, V _{NO} , V _{NC} = V _{COM} = 0.3 V/3.3 V	Room Full	- 2 - 20		2 20	
Digital Control			-				
Input High Voltage ^d	V _{INH}		Full	1.4			v
Input Low Voltage	V _{INL}		Full			0.5	v
Input Capacitance	C _{in}		Full		8		pF
Input Current ^f	$I_{\rm INL}$ or $I_{\rm INH}$	V _{IN} = 0 or V+	Full	1		1	μA

Vishay Siliconix



SPECIFICATIONS (V+ = 3 V)							
		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °C		5 °C	
Parameter	Symbol	V+ = 2.7 to 3.6 V, V_{IN} = 0.5 V or 1.4 V e	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Dynamic Characteristics							
Turn-On Time	t _{ON}	V+ = 2.7 V, V _{NO} or V _{NC} = 1.5 V	Room Full		16	46 48	20
Turn-Off Time	t _{OFF}	R_L = 300 Ω, C_L = 35 pF	Room Full		7	37 39	ns
Charge Injection ^d	Q _{INJ}	${ m C_L}$ = 1 nF, ${ m V_{GEN}}$ = 2 V, ${ m R_{GEN}}$ = 0 Ω	Room		1		рС
Off-Isolation ^d	OIRR		Room		- 78.5		
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 113		
Off-Isolation ^d	OIRR	R ₁ = 50 Ω, C ₁ = 5 pF, f = 10 MHz	Room		- 58		dB
Crosstalk ^d	X _{TALK}	$m_{L} = 50.52, G_{L} = 5 \text{ pr}, T = 10 \text{ Mmz}$	Room		- 66		
0" 0	C _{NO/NC(off)}		Room		8		
Off Capacitance ^d	C _{COM(off)}	$V_{IN} = 0$ or V+, f = 1 MHz	Room		14		~E
Channel On Canaditanaad	C _{NO/NC(on)}	$v_{\rm IN} = 0.01$ $v_{\rm T}$, $t = 1.001$ $t_{\rm Z}$	Room		27		pF
Channel-On Capacitance ^d	C _{COM(on)}]			27		
Power Supply							
Power Supply Current	l+	V _{IN} = 0 or V+	Room Full		0.001	1.0 1.0	μΑ



Vishay Siliconix

SPECIFICATIONS (V+ = 5 V)							
		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °C			
Parameter	Symbol	V+ = 4.2 to 5.5 V, V _{IN} = 0.8 V or 2.0 V ^e	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Analog Switch					•	•	
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	v
On-Resistance ^d	R _{ON}		Room Full		2.6	3.5 3.7	
r _{ON} Flatness ^d	R _{ON} Flatness	V+ = 4.2 V, V _{COM} = 0.5/3.5 V I _{NO} , I _{NC} = 10 mA	Room		0.8	1.2	Ω
On-Resistance Match Between Channels ^d	$\Delta R_{DS(on)}$		Room			0.2	
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}	$V_{+} = 5.5 V,$	Room Full	- 2 - 20		2 20	
Switch On Leakage Guneni	I _{COM(off)}	V_{NO} , V_{NC} = 1.0 V/4.5 V, V_{COM} = 4.5 V/1.0 V RC		- 2 - 20		2 20	nA
Channel-On Leakage Current	I _{COM(on)}	V+ = 5.5 V, V _{NO} , V _{NC} = V _{COM} = 1.0 V/4.5 V	Room Full	- 2 - 20		2 20	
Digital Control							
Input High Voltage ^d	V _{INH}		Full	2.0			v
Input Low Voltage	V _{INL}		Full			0.8	•
Input Capacitance	C _{in}		Full		8		pF
Input Current	$I_{\rm INL}$ or $I_{\rm INH}$	V _{IN} = 0 or V+	Full	1		1	μΑ
Dynamic Characteristics							
Turn-On Time	t _{ON}	V+ = 4.2 V, V _{NO} or V _{NC} = 3.0 V	Room Full		11	41 43	ns
Turn-Off Time	t _{OFF}	R_L = 300 Ω, C_L = 35 pF	Room Full		7	37 39	no
Charge Injection ^d	Q _{INJ}	${\sf C}_{\sf L}$ = 1 nF, ${\sf V}_{\sf GEN}$ = 2 V, ${\sf R}_{\sf GEN}$ = 0 Ω	Room		1		рС
Off Operations of	C _{NO/NC(off)}		Room	8			
Off Capacitance ^d	C _{COM(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		14		nE
Channel-On Capacitance ^d	C _{NO/NC(on)}	$v_{\rm IN} = 0.01$ $v_{\rm T}$, $t = 1.0012$	Room		28		pF
Channel-On Capacitance"	C _{COM(on)}	Ro			28		
Power Supply			· ·				
Power Supply Current	l+	V _{IN} = 0 or V+	Room Full		0.001	1.0 1.0	μA

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

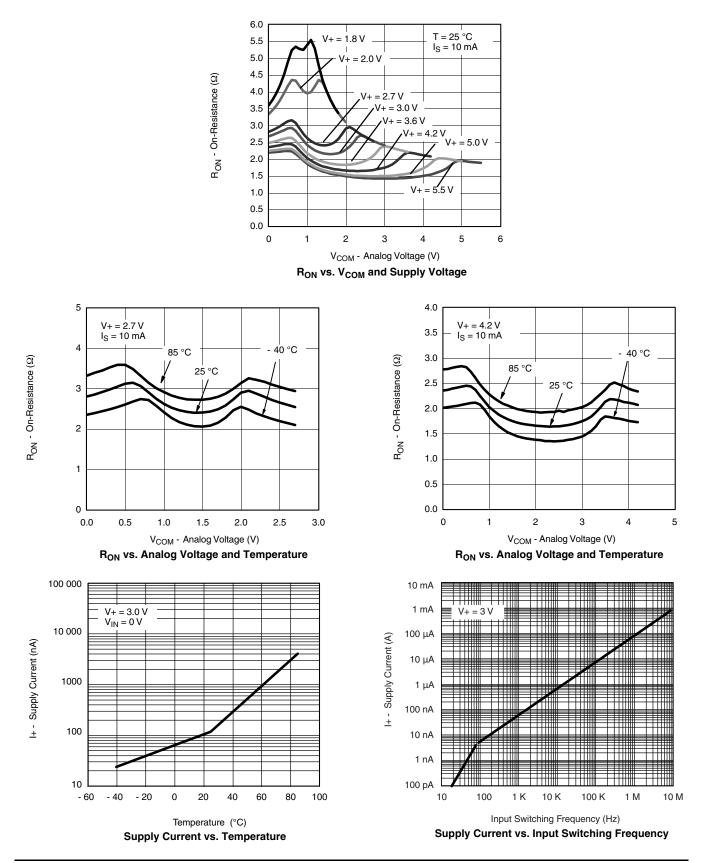
d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

f. Guaranteed by 5 V leakage testing, not production tested.



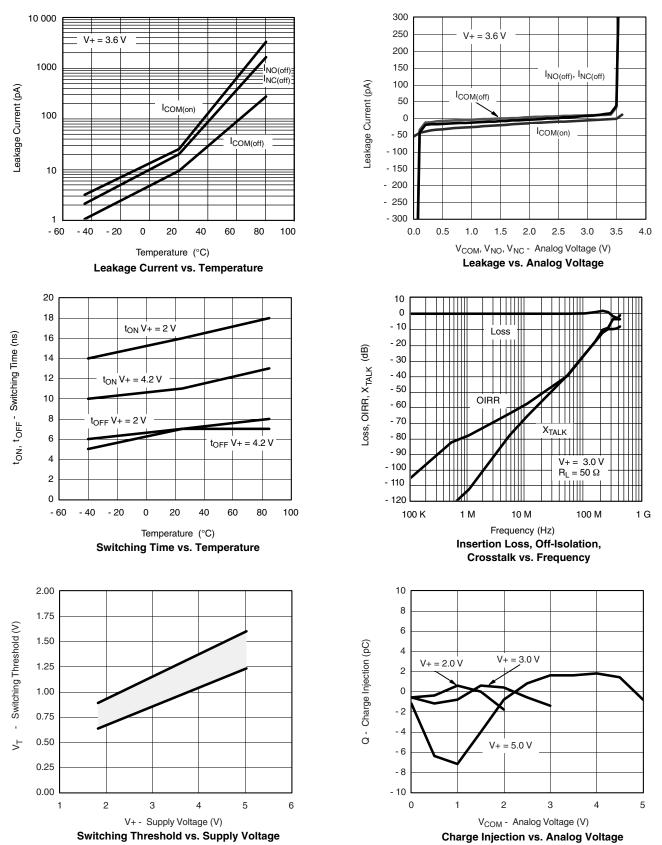
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





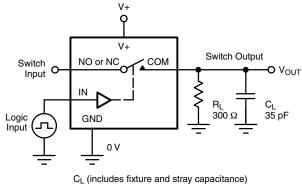
Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

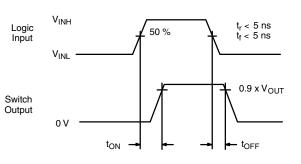


Vishay Siliconix

TEST CIRCUITS

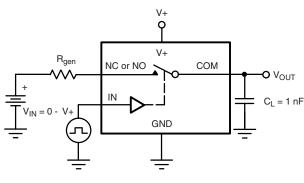


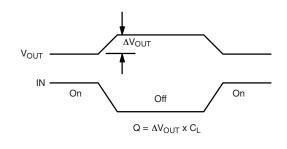




Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

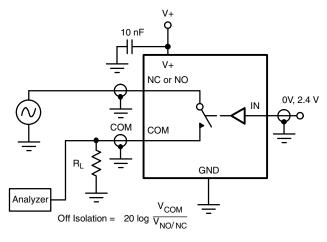




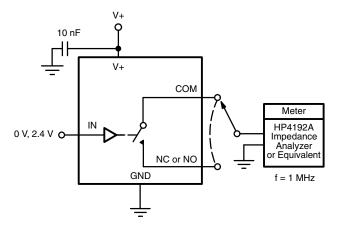


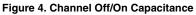
IN depends on switch configuration: input polarity determined by sense of switch.











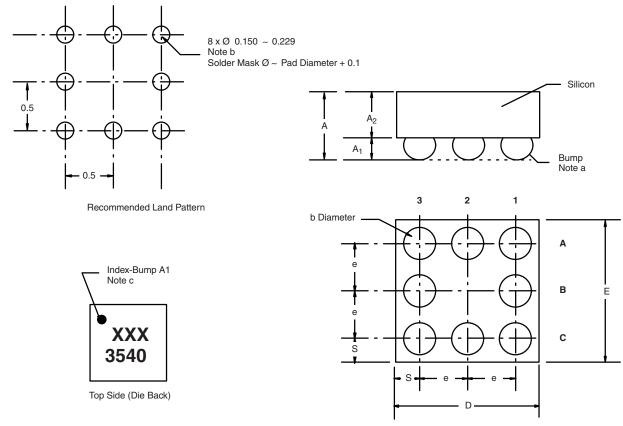




Vishay Siliconix

PACKAGE OUTLINE

MICRO FOOT: 8 BUMP (3 x 3, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)



Notes (Unless Otherwise Specified):

a. Bump is Lead (Pb)-free Sn/Ag/Cu.

b. Non-solder mask defined copper landing pad.

c. Laser Mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

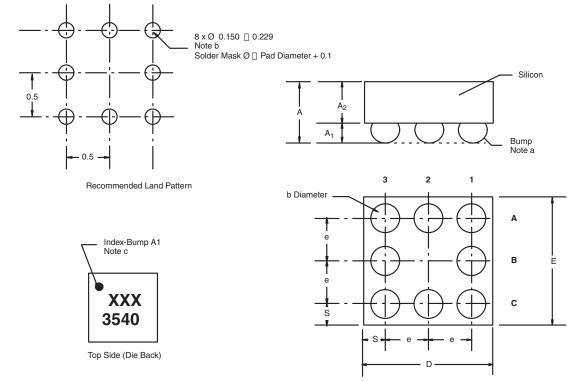
	Millim	Millimeters ^a		nes
Dim.	Min.	Max.	Min.	Max.
Α	0.688	0.753	0.0271	0.0296
A ₁	0.218	0.258	0.0086	0.0102
A ₂	0.470	0.495	0.0185	0.0195
b	0.306	0.346	0.0120	0.0136
D	1.480	1.520	0.0583	0.0598
E	1.480	1.520	0.0583	0.0598
е	0.5 BASIC		0.0197	BASIC
S	0.230	0.270	0.0091	0.0106

Notes:

a. Use millimeters as the primary measurement.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73320.





MICRO FOOT: 8-BUMP (3 mm x 3 mm, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)

Notes

- (unless otherwise specified)
- a. Bump is lead (Pb)-free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.

c. Laser mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

DIM.	MILLIM	ETERS ^a	INC	HES	
Diwi.	MIN.	MAX.	MIN.	MAX.	
A	0.688	0.753	0.0271	0.0296	
A ₁	0.218	0.258	0.0086	0.0102	
A ₂	0.470	0.495	0.0185	0.0195	
b	0.306	0.346	0.0120	0.0136	
D	1.480	1.520	0.0583	0.0598	
E	1.480	1.520	0.0583	0.0598	
e	0.5 B	ASIC	0.0197 BASIC		
S	0.230	0.270	0.0091	0.0106	

Note

a. Use millimeters as the primary measurement.

ECN: S11-1065-Rev. A, 13-Jun-11 DWG: 6002

www.vishay.com 1

This document is subject to change without notice. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.